

40V PNP HIGH GAIN LOW SATURATION MEDIUM POWER TRANSISTOR

Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirement of automotive applications.

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.05 grams (Approximate)

Features

- BV_{CEO} > -40V
- I_C = -5.5A Continuous Collector Current
- I_{CM} = -15A Peak Pulse Current
- Very Low Saturation Voltage V_{CE(SAT)} < -60mV max @ -1A
- R_{SAT} = 29mΩ @ -5.5A for Low Equivalent On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

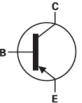
Applications

- DC-DC Converters
- MOSFET Gate Drivers
- · Charging Circuits
- Power Switches
- Motor Control

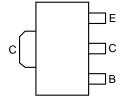
SOT89



Top View



Device Schematic



Pin-Out Top View

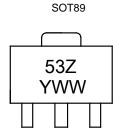
Ordering Information (Notes 4 and 5)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTP2009ZQTA	53Z	7	12	1000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q10x qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



53Z = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year (ex: 8 = 2018) WW = Week code (01 - 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Base Voltage	V _{CBS}	-50	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-5.5	А
Peak Pulse Current	I _{CM}	-15	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 6)		0.9 7.2	w	
Power Dissipation	(Note 7)	D	1.5 12		
Linear Derating Factor	(Note 8)	P_{D}	2.1 16.8	mW/°C	
	(Note 9)		3 24	1	
	(Note 6)	R _{OJA}	139		
Thermal Desigtance Junction to Ambient	(Note 7)	_	83	°C/W	
Thermal Resistance, Junction to Ambient	(Note 8)	_	60	C/VV	
	(Note 9)	R _{OJA}	42		
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

Notes:

^{6.} For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in steady-state.

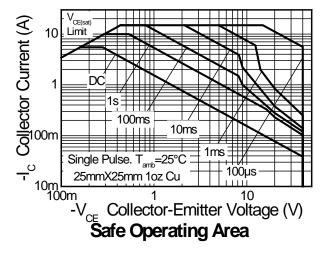
^{7.} Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.

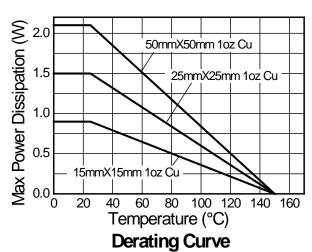
^{8.} Same as Note 6, except the device is mounted on 50mm x 50mm 1oz copper.
9. Same as Note 6, except the device is mounted on 25mm x 25mm measured at t<5 secs.

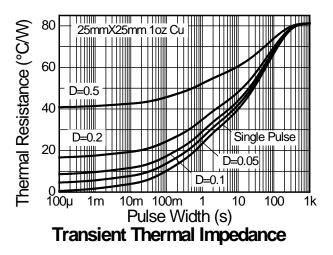
^{10.}Refer to JEDEC specification JESD22-A114 and JESD22-A115.

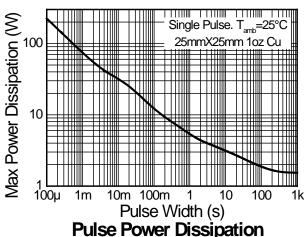


Thermal Characteristics and Derating Information











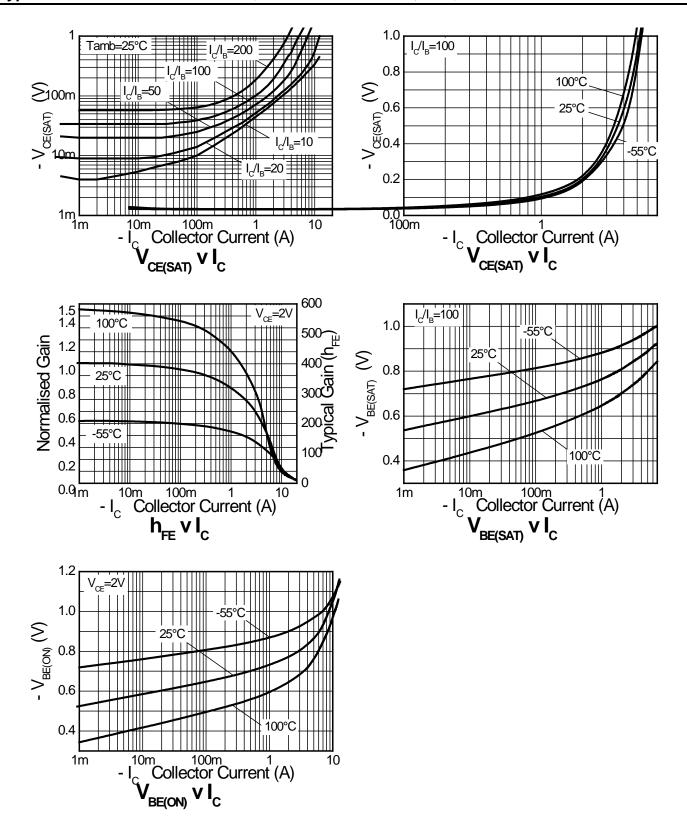
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage	BV _{CBO}	-50	-90	_	V	I _C = -100μA	
Collector-Emitter Breakdown Voltage	BV _{CER}	-50	-90	_	V	$I_C = -1\mu A, R_B \le 1k\Omega$	
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-40	-58	_	V	I _C = -10mA	
Emitter-Base Breakdown Voltage	BV _{EBO}	-7.5	-8.3	_	V	I _E = -100μA	
Collector Cutoff Current	I _{CBO}	_	< -1	-20	nA	V _{CB} = -40V	
Collector Cutoff Current	I _{CES}	_	< -1	-20	nA	V _{CB} = -32V	
Emitter Cutoff Current	I _{EBO}	_	< -1	-20	nA	V _{EB} = -6V	
Collector-Emitter Saturation Voltage (Note 11)	V _{CE} (SAT)	_	-15 -44 -50 -120 -70 -125 -130 -162	-30 -60 -70 -165 -80 -175 -175	mV	I _C = -0.1A, I _B = -10mA I _C = -1A, I _B = -100mA I _C = -1A, I _B = -50mA I _C = -1A, I _B = -10mA I _C = -2A, I _B = -200mA I _C = -2A, I _B = -40mA I _C = -3.5A, I _B = -175mA I _C = -5.5A, I _B = -550mA	
Base-Emitter Saturation Voltage (Note 11)	V _{BE(SAT)}	_	-820 -1000	-900 -1075	mV	$I_C = -2A$, $I_B = -40mA$ $I_C = -5.5A$, $I_B = -550mA$	
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(ON)}	_	-778 -869	-850 -950	mV	$I_C = -2A$, $V_{CE} = -2V$ $I_C = -5.5A$, $V_{CE} = -2V$	
DC Current Gain (Note 11)	h _{FE}	200 200 170 110	390 350 290 175	550	_	I _C = -10mA, V _{CE} = -2V I _C = -0.5A, V _{CE} = -2V I _C = -2A, V _{CE} = -2V I _C = -5.5A, V _{CE} = -2V	
Transition Frequency	f _T	_	152	_	MHz	$V_{CE} = -10V, I_{C} = -50mA,$ f = 100MHz	
Output Capacitance (Note 11)	C _{OBO}	_	53	_	рF	$V_{CB} = -10V$, $f = 1MHz$	
	t_d	_	18	_	ns		
	t _r	_	17	_		$V_{CC} = -10V, I_{C} = -1A,$	
Switching Times	t _s	_	325			$I_{B1} = -I_{B2} = -100 \text{mA}$	
	t _r —	60	_				
	t _d	_	55	_	ns	V _{CC} = -30V, I _C = -2A,	
Switching Times	t _r	_	107	_			
Owntolling Tilles	t _s	_	264	_	119	$I_{B1} = -I_{B2} = -20mA$	
	t _r	_	103	_			

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



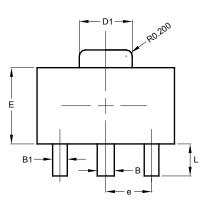
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

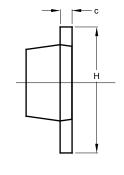




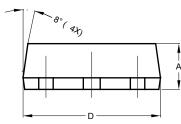
Package Outline Dimensions

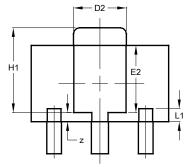
Please see http://www.diodes.com/package-outlines.html for the latest version.





SOT89

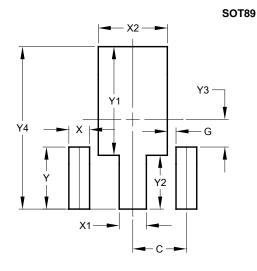




SOT89						
Dim	Min	Max	Тур			
Α	1.40	1.60	1.50			
В	0.50	0.62	0.56			
B1	0.42	0.54	0.48			
С	0.35	0.43	0.38			
D	4.40	4.60	4.50			
D1	1.62	1.83	1.733			
D2	1.61	1.81	1.71			
Е	2.40	2.60	2.50			
E2	2.05	2.35	2.20			
е		_	1.50			
Н	3.95	4.25	4.10			
H1	2.63	2.93	2.78			
L	0.90	1.20	1.05			
L1	0.327	0.527	0.427			
Z	0.20	0.40	0.30			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value
Dilliensions	(in mm)
С	1.500
G	0.244
Х	0.580
X1	0.760
X2	1.933
Υ	1.730
Y1	3.030
Y2	1.500
Y3	0.770
V۵	4 530



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